MA2417Y10000000

P-Ch 20V Fast Switching MOSFETs

General Description

The MA2417Y1 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The MA2417Y1 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

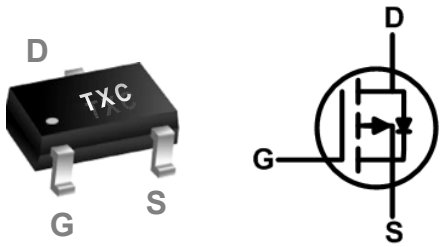
Product Summery

BVDSS	RDSON	ID
-20V	240mΩ	-1A

Applications

- High Frequency Point-of-Load Synchronous s Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT323 (SC-70-3L) Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ -4.5V[1]	-1	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ -4.5V[1]	-0.8	A
I_{DM}	Pulsed Drain Current[2]	-5	A
P_D@T_A=25°C	Total Power Dissipation[3]	0.33	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	375	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	240	°C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I_D=-1mA	---	-0.012	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V , I_D=-1A	---	185	240	mΩ
		V_{GS}=-2.5V , I_D=-0.5A	---	270	350	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.5	-0.8	-1.2	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	2.2	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-16V , V_{GS}=0V , T_J=25°C	---	---	-1	uA
		V_{DS}=-16V , V_{GS}=0V , T_J=55°C	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-1A	---	3.1	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	39	78	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-1A	---	2.9	4.1	nC
Q_{gs}	Gate-Source Charge		---	0.51	0.7	
Q_{gd}	Gate-Drain Charge		---	0.81	1.1	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-10V , V_{GS}=-4.5V , R_G=3.3Ω , I_D=-1A	---	2	4.0	ns
T_r	Rise Time		---	8	14.4	
$T_{d(off)}$	Turn-Off Delay Time		---	23	46	
T_f	Fall Time		---	14.8	29.6	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	190	266	pF
C_{oss}	Output Capacitance		---	33	46.2	
C_{rss}	Reverse Transfer Capacitance		---	27	37.8	

Drain-Source Body Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source-Drain Diode Current[1,4]	V_G=V_D=0V , Force Current	---	---	-1	A
I_{SM}	Pulsed Diode Forward Current[2,4]		---	---	-5	A
V_{SD}	Body Diode Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25°C	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-2A , dI/dt=100A/μs , T_J=25°C	---	6.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	2	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150°C junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

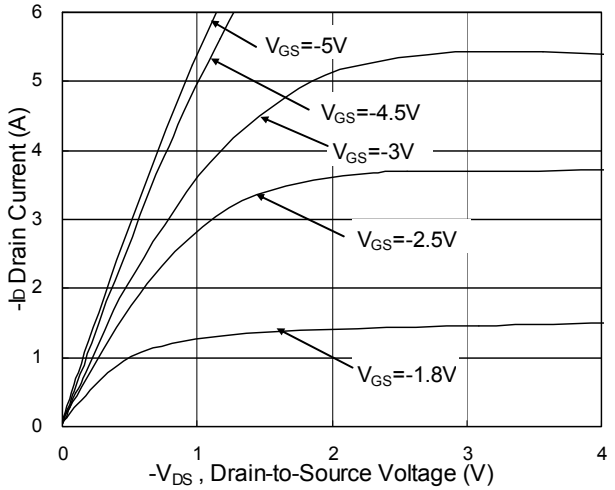


Fig.1 Typical Output Characteristics

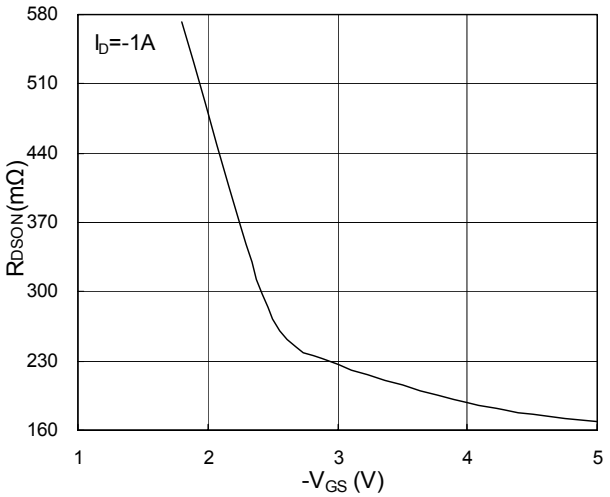


Fig.2 On-Resistance vs. Gate-Source

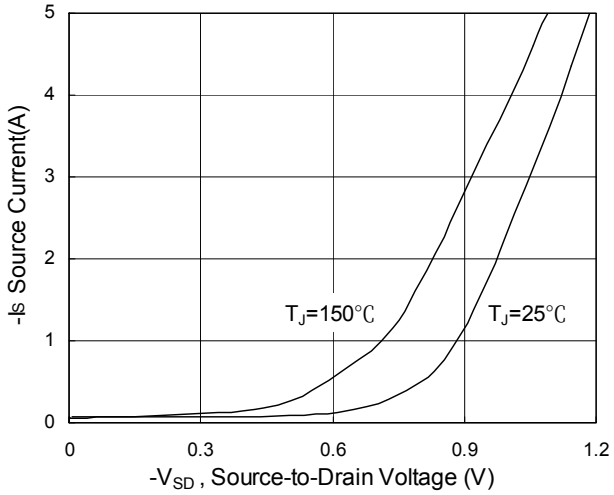


Fig.3 Forward Characteristics Of Reverse

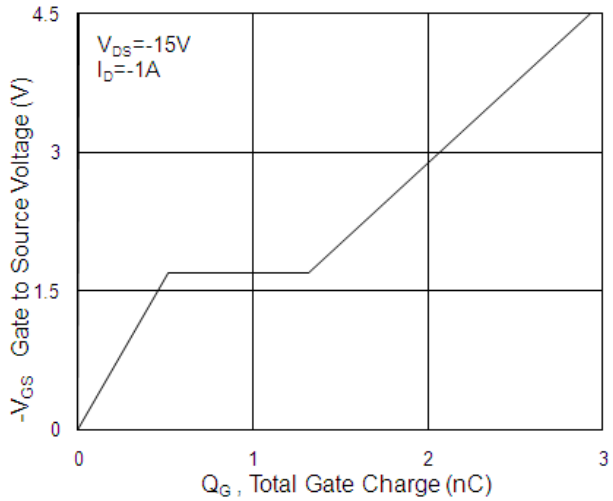


Fig.4 Gate-Charge Characteristics

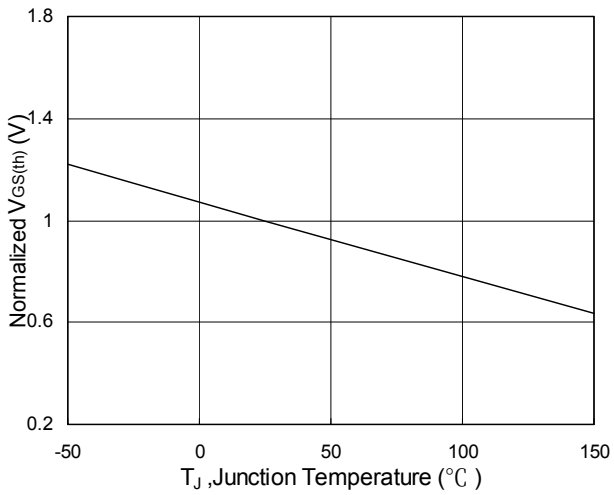


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

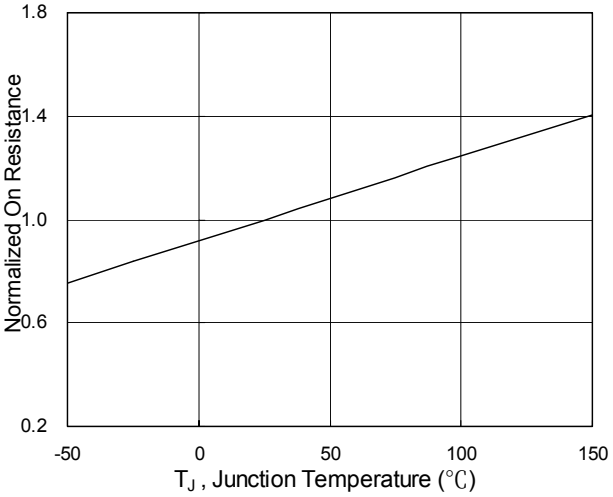


Fig.6 Normalized R_{DSON} vs. T_J

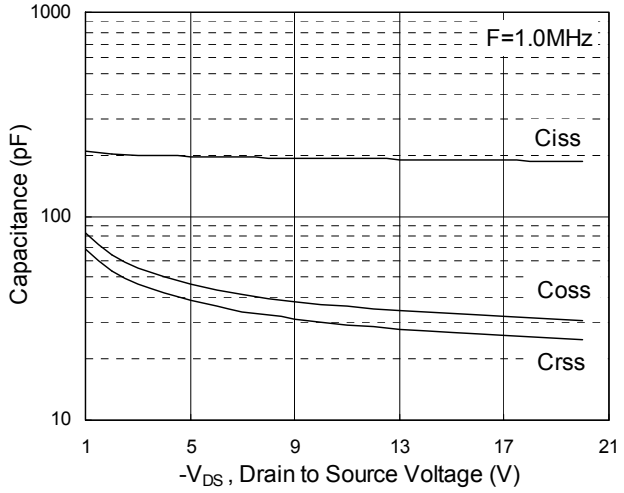


Fig.7 Capacitance

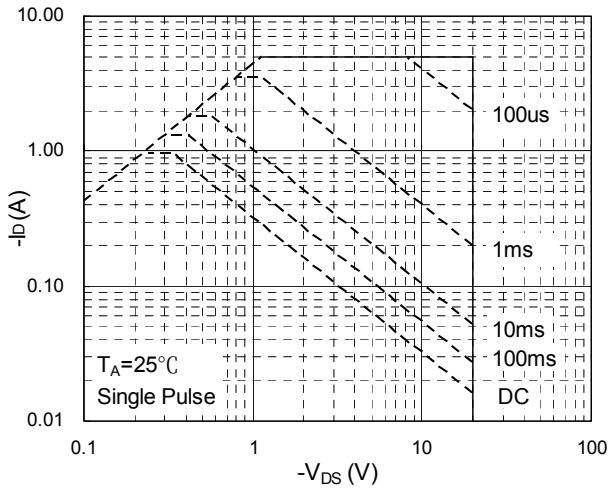


Fig.8 Safe Operating Area

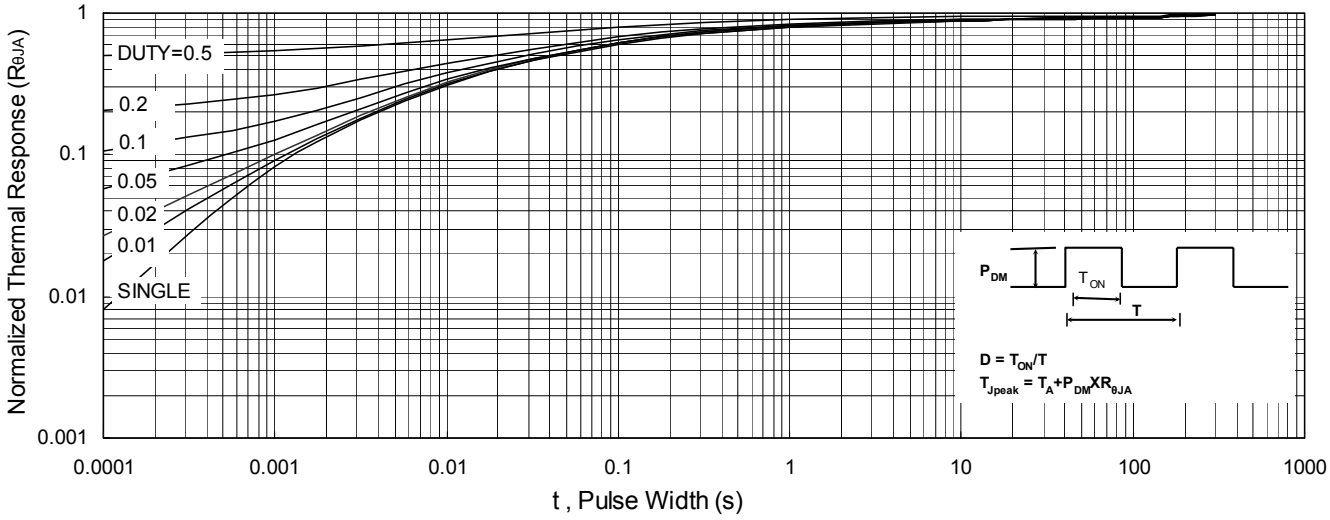


Fig.9 Normalized Maximum Transient Thermal Impedance

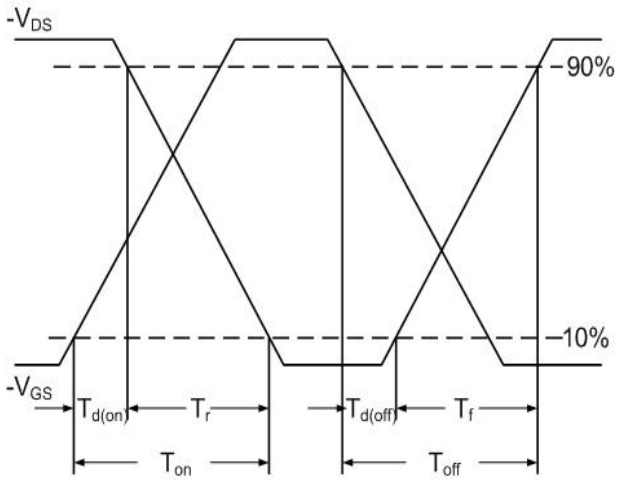


Fig.10 Switching Time Waveform

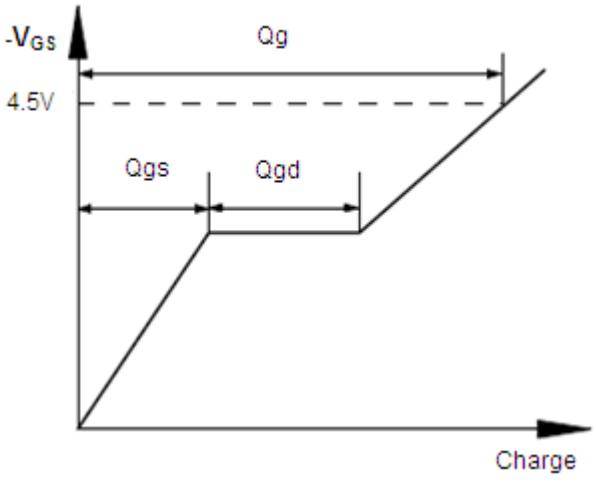
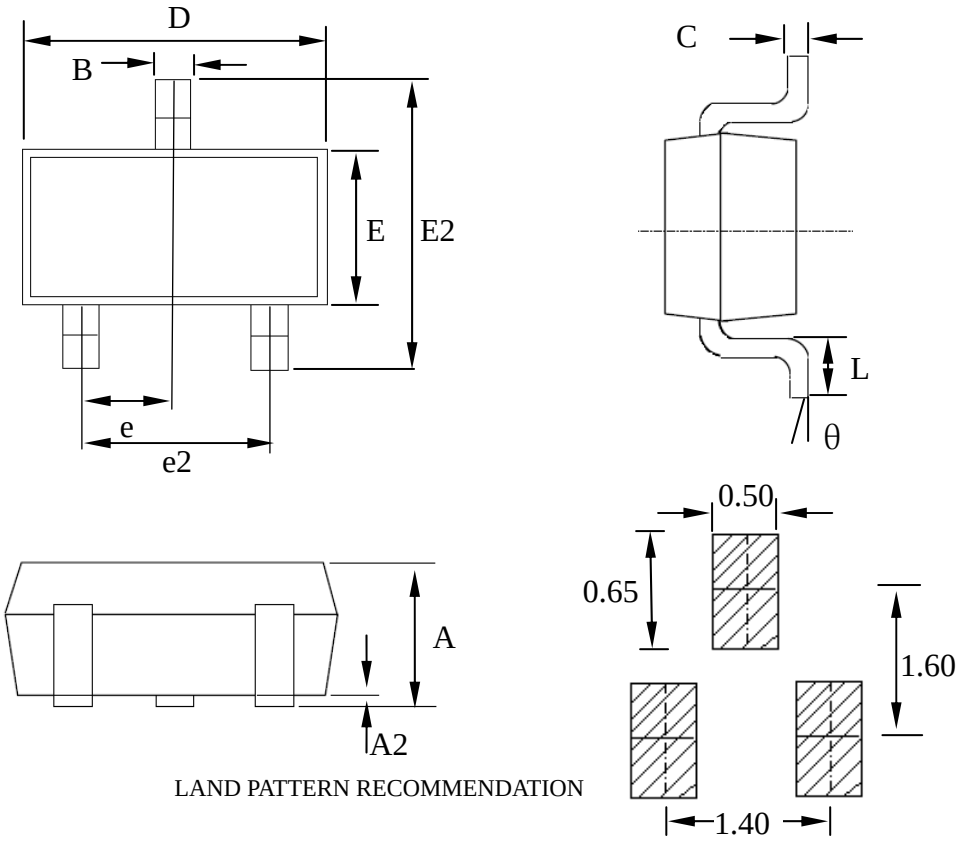


Fig.11 Gate Charge Waveform

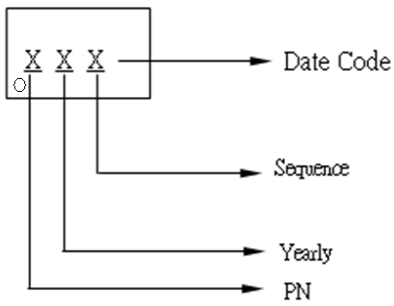
SOT-323 Outline



LAND PATTERN RECOMMENDATION

2.CONTROLLING DIMENSION IS MILLIMETER CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACTLY.

MARKING

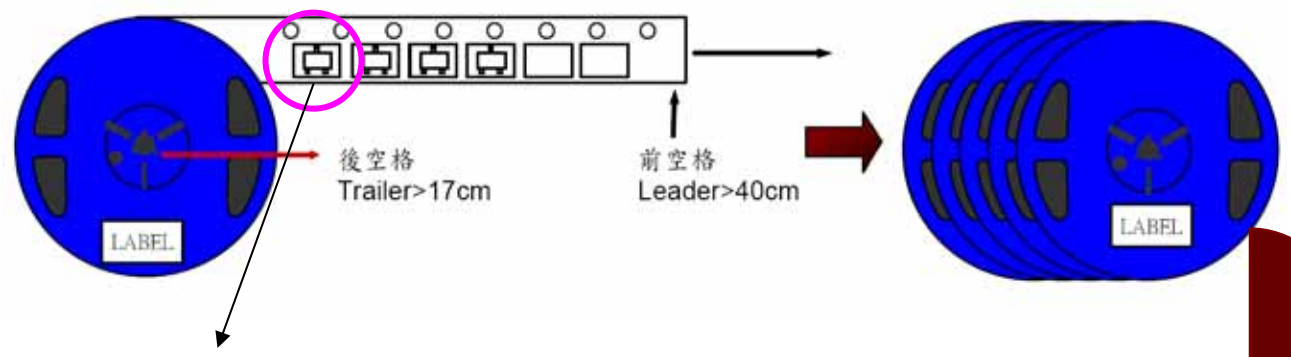


SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	--	1.10	0.035	--	0.043
A2	0.00	--	0.10	0.000	--	0.004
B	0.15	--	0.40	0.006	--	0.016
C	0.08	--	0.20	0.003	--	0.008
D	2.00	--	2.20	0.079	--	0.087
E	1.15	--	1.40	0.045	--	0.055
E2	2.15	--	2.45	0.085	--	0.096
e	--	0.65	--	--	0.026	--
e2	1.20	--	1.40	0.047	--	0.055
L	0.26	--	0.46	0.010	--	0.018
θ	0°	--	8°	0°	--	8°

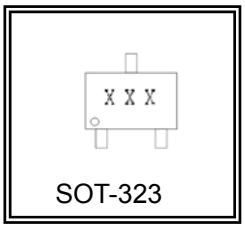
Note:

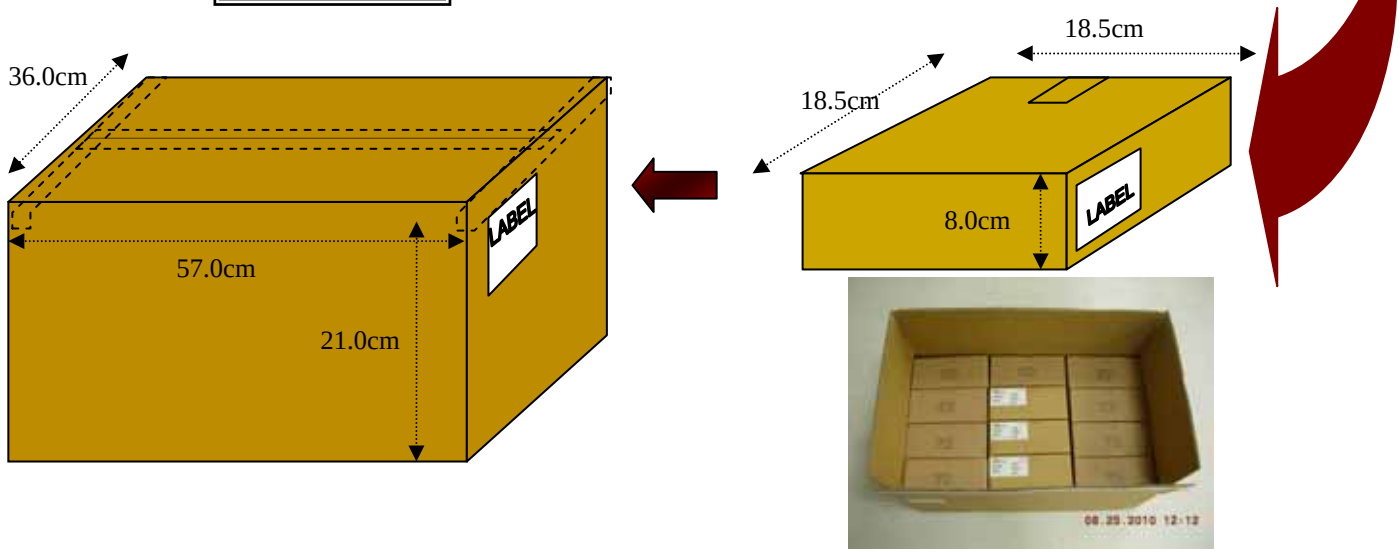
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. CONTROLLING DIMENSION IS MILLIMETER CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACTLY.

Tape & Reel 繞捲及裝箱方式 – 適用 SOT-323



產品正印及方向 –（正印為正時，Tape 圓孔在上方）





封裝形態 PKG TYPE	一 般 包 裝		
	一卷數量 Immediate Quantity	中箱數量 Intermediate Quantity	外箱裝置/數量 Carton Quantity
OT-23/25 TSOP-5/6 SOT-363 / 323	3000pcs	15000pcs	180 K
	Reel（7”）	Box(5 reels)	Carton(12 Box)